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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Patent Application )  
 )  
Applicant: Kozo NAKAMURA, Toshiaki )  
 SAISHOJI, Hirotaka NAKAJIMA, )  
 Shinya SADOHARA, Masashi )  
 NISHIMURA, Toshiro KOTOOKA, )  
 AND Yoshiyuki SHIMANUKI )  
 )  
Serial No.: Not Yet Assigned )  
 )  
Filed: Herewith )  
 )  
For: PRODUCTION METHOD FOR SILICON SINGLE )  
 CRYSTAL AND PRODUCTION DEVICE FOR )  
 SINGLE CRYSTAL INGOT, AND HEAT )  
 TREATING METHOD FOR SILICON SINGLE )  
 CRYSTAL WAFER )  
 )  
 )

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

This is a Preliminary Amendment for entry in the above-identified application.

In the Claims:

Please amend claims as follows:

A 3. (amended) The method for producing a silicon single crystal ingot according  
to Claim 1, characterized in that said conditions (a) and (b) are adjusted by changing the pulling  
speed of the silicon single crystal ingot when the silicon single crystal ingot is produced by the  
Czochralski method.